

Notice of References Cited		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		10/566,522	JIN ET AL.	
Examiner		Art Unit		Page 1 of 1
JAMI M. VALENTINE		2894		

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*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A US-2005/0111256	05-2005	Bednorz et al.	365/177
*	B US-7,099,141	08-2006	Kaufman et al.	361/311
C	US-			
D	US-			
E	US-			
F	US-			
G	US-			
H	US-			
I	US-			
J	US-			
K	US-			
L	US-			
M	US-			

FOREIGN PATENT DOCUMENTS

*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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T					

NON-PATENT DOCUMENTS

*	Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
U	Beck et al. ("Reproducible switching effect in thin oxide films for memory applications" Applied Physics Letters, Vol. 77, No. 1, July 2000, page 139)
V	Watanabe et al ("Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO ₃ single crystals" Applied Physics Letters, Vol. 78, No. 23, June 2001 page 3738)
W	Rossei et al ("Electrical current distribution across a metal-insulator-metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, September 2001, page 2892)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a))
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.